

STPS40SM100C

Datasheet

100 V, 40 A power Schottky rectifier





TO-220AB

Features

- Low forward voltage drop
- Good trade-off between leakage current and forward voltage drop
- High frequency operation
- Avalanche capability specified
- ECOPACK[®]2 compliant

Applications

- Switching diode
- SMPS
- DC/DC converter
- LED lighting
- Adapter for notebook and game station

Description

The STPS40SM100C is suited for high frequency switch mode power supply.

Packaged in TO-220AB, the STPS40SM100C is optimized for use in notebook and game station adaptors, providing in these applications a good efficiency at both low and high load.

Product status link			
STPS40SM100C			
Product summary			
Symbol Value			
I _{F(AV)}	2 x 20 A		
V_{RRM} 100 V			
T _j (max.) 150 °C			
V_F (typ.) 0.605 ∨			

1 Characteristics

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Table 1. Absolute Ratings (limiting values, per diode, at 25 °C, unless otherwise specified)

Symbol	Parameter			Value	Unit
V _{RRM}	Repetitive peak reverse voltage			100	V
I _{F(RMS)}	Forward rms current			60	Α
		T _C = 130 °C	Per diode	20	•
I _{F(AV)}	Average forward current, $\delta = 0.5$ square wave	T _C = 125 °C	Per device	40	A
I _{FSM}	Surge non repetitive forward current	on repetitive forward current t_p = 10 ms sinusoidal			Α
P _{ARM}	Repetitive peak avalanche power $t_p = 10 \ \mu s$, $T_j = 125 \ ^{\circ}C$			1295	W
T _{stg}	Storage temperature range			-65 to +175	°C
Tj	Maximum operating junction temperature ⁽¹⁾			150	°C

1. $(dP_{tot'}/dT_j) < (1/R_{th(j-a)})$ condition to avoid thermal runaway for a diode on its own heatsink.

Table 2. Thermal resistance parameters

Symbol	Parameter		Max. value	Unit
P	lunction to case	Per diode	1.3	
R _{th(j-c)} Junction to case	Total	0.7	°C/W	
R _{th(c)}	Coupling		0.1	

When the diodes 1 and 2 are used simultaneously:

 $\Delta T_{j \text{ (diode1)}} = P_{\text{(diode1)}} \times R_{\text{th}(j-c)} \text{ (per diode)} + P_{\text{(diode2)}} \times R_{\text{th}(c)}$

For more information, please refer to the following application note :

AN5088 : Rectifiers thermal management, handling and mounting recommendations

Table 3. Static electrica	I characteristics	(per diode)
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Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
		T _j = 25 °C	V _R = 70 V	-	7		μA
I_ (1)	Deverse leakage surrent	T _j = 125 °C	VR - 70 V	-	7		mA
IR (1)	I _R ⁽¹⁾ Reverse leakage current	T _j = 25 °C	V _R = 100 V	-	13	45	μA
		T _j = 125 °C	VR - 100 V	-	13	45	mA
		T _j = 25 °C	I _F = 5 A	-	520		-
		T _j = 125 °C		-	435		
V _F ⁽²⁾	Forward valtage drag	T _j = 25 °C	1 - 10 4	-	620	700	
VF Forward VC	Forward voltage drop	T _j = 125 °C	I _F = 10 A	-	520	580	mV
		T _j = 25 °C	L = 20 A	-	740	810	
		T _j = 125 °C	I _F = 20 A	-	605	665	

1. Pulse test: $t_p = 5 ms$, $\delta < 2\%$

2. Pulse test: $t_p = 380 \ \mu s, \ \delta < 2\%$

To evaluate the conduction losses, use the following equation: $P = 0.580 \times I_{F(AV)} + 0.0043 \times I_{F}^{2} (RMS)$ For more information, please refer to the following application notes related to the power losses :

- AN604: Calculation of conduction losses in a power rectifier
- AN4021: Calculation of reverse losses on a power diode



1.1 Characteristics (curves)









Figure 7. Forward voltage drop versus forward current (per diode)



2 Package information

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In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

2.1 TO-220AB package information

- Epoxy meets UL 94,V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 N·m
- Maximum torque value: 0.70 N·m

Figure 8. TO-220AB package outline



	Dimensions				
Ref.	Millin	Millimeters		ference only)	
	Min.	Max.	Min.	Max.	
А	4.40	4.60	0.173	0.181	
b	0.61	0.88	0.240	0.035	
b1	1.14	1.55	0.045	0.061	
С	0.48	0.70	0.019	0.028	
D	15.25	15.75	0.600	0.620	
D1	1.27	′ typ.	0.050 typ.		
E	10.00	10.40	0.394	0.409	
е	2.40	2.70	0.094	0.106	
e1	4.95	5.15	0.195	0.203	
F	1.23	1.32	0.048	0.052	
H1	6.20	6.60	0.244	0.260	
J1	2.40	2.72	0.094	0.107	
L	13.00	14.00	0.512	0.551	
L1	3.50	3.93	0.138	0.155	
L20	16.4	16.40 typ.		δ typ.	
L30	28.9	28.90 typ.		З typ.	
θΡ	3.75	3.85	0.148	0.152	
Q	2.65	2.95	0.104	0.116	

Table 4. TO-220AB package mechanical data



3 Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPS40SM100CT	PS40SM100CT	TO-220AB	1.95 g	50	Tube

Revision history

Date	Version	Changes
25-Mar-2009	1	First issue.
15-Apr-2010	2	Updated package graphics for TO-220AB on front page and in Table 5
27-Jun-2018	3	Updated Table 1. Absolute Ratings (limiting values, per diode, at 25 °C, unless otherwise specified) and Figure 3. Normalized avalanche power derating versus pulse duration (T_j = 125 °C). Removed I ² PAK and D ² PAK package information.
22-Feb-2019	4	Updated Table 1.

Table 6. Document revision history



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